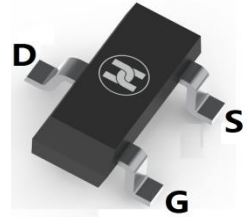
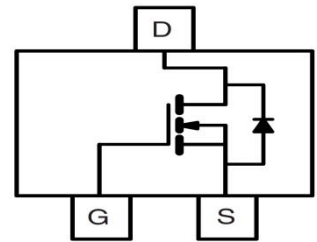


HIGH VOLTAGE MOSFET (N-CHANNEL)
FEATURES

- $V_{DS}=100V, R_{DS(ON)}=1\Omega @ V_{GS}=10V, I_D=0.64A$
- Low on-resistance and Low threshold
- Fast switching speed
- Low gate drive
- For Relay and Solenoid driving , Motor control applications
- For DC - DC Converters and Power Management Functions
- Surface Mount device


SOT-23
MECHANICAL DATA

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.008 grams (approximate)


MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current	I_D	0.64	A
Pulsed drain current	I_{DM}	2.5	A
Continuous Source Current (Body Diode)	I_S	2	A
Pulsed Source Current (Body Diode)	I_{SM}	2.5	A
Power dissipation	P_D	625	mW
Junction to Ambient	$R_{\theta JA}$	200	°C/W
Junction temperature	T_J	150	°C
Storage temperature	T_{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Drain-Source breakdown voltage	$V_{(BR)DSS}$	100			V	$V_{GS}=0V, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}			1	μA	$V_{DS}=60V, V_{GS}=0V$
Gate-body leakage current	I_{GSS}			100	nA	$V_{DS}=0V, V_{GS}=\pm 20V$
Gate-threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Drain-source on-resistance (note 1)	$R_{DS(ON)}$			1	Ω	$V_{GS}=10V, I_D=1.5A$
				1.1	Ω	$V_{GS}=6V, I_D=1A$
Forward Trans-conductance(note 1,2)	g_{fs}		1.6		S	$V_{DS}=15V, I_D=1A$
Input capacitance(note2)	C_{iss}		138		pF	$V_{DS}=60V, V_{GS}=0V, f=1MHz$
Output capacitance(note2)	C_{oss}		12		pF	
Reverse transfer capacitance(note2)	C_{rss}		6		pF	
Turn-on delay time(note2,3)	$t_{d(on)}$		1.8		nS	
Turn-on rise time(note2,3)	t_r		1.5		nS	$V_{DS}=50V, V_{GS}=10V, I_D=1.0A, R_G=6.0\Omega$
Turn-off delay time(note2,3)	$t_{d(off)}$		4.1		nS	
Turn-off fall time(note2,3)	t_f		2.1		nS	
Total Gate Charge(note2,3)	Q_g		2.9		nC	$V_{DS}=50V, V_{GS}=10V, I_D=1.0A$
Gate-Source Charge(note2,3)	Q_{gs}		0.7		nC	
Gate-Drain Charge(note2,3)	Q_{gd}		1		nC	
Diode Forward Voltage(note 1)	V_{SD}			0.95	V	$V_{GS}=0V, I_S=1.5A, T_J=25^\circ C$
Reverse Recovery Time(note 3)	t_{rr}		27		nS	$I_F=1.8A, T_J=25^\circ C, di/dt=100A/\mu S$
Reverse Recovery Charge(note 3)	Q_{rr}		12		nC	

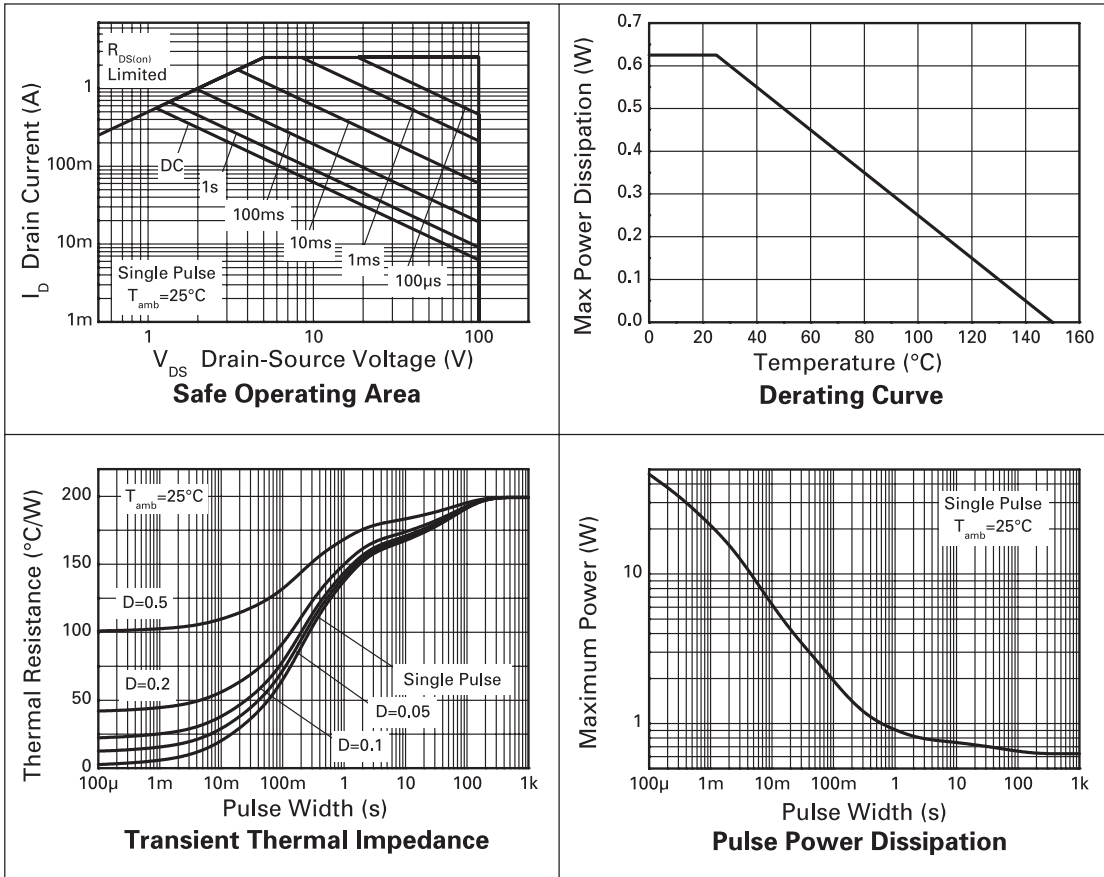
Note:(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$

(2) Sample test.

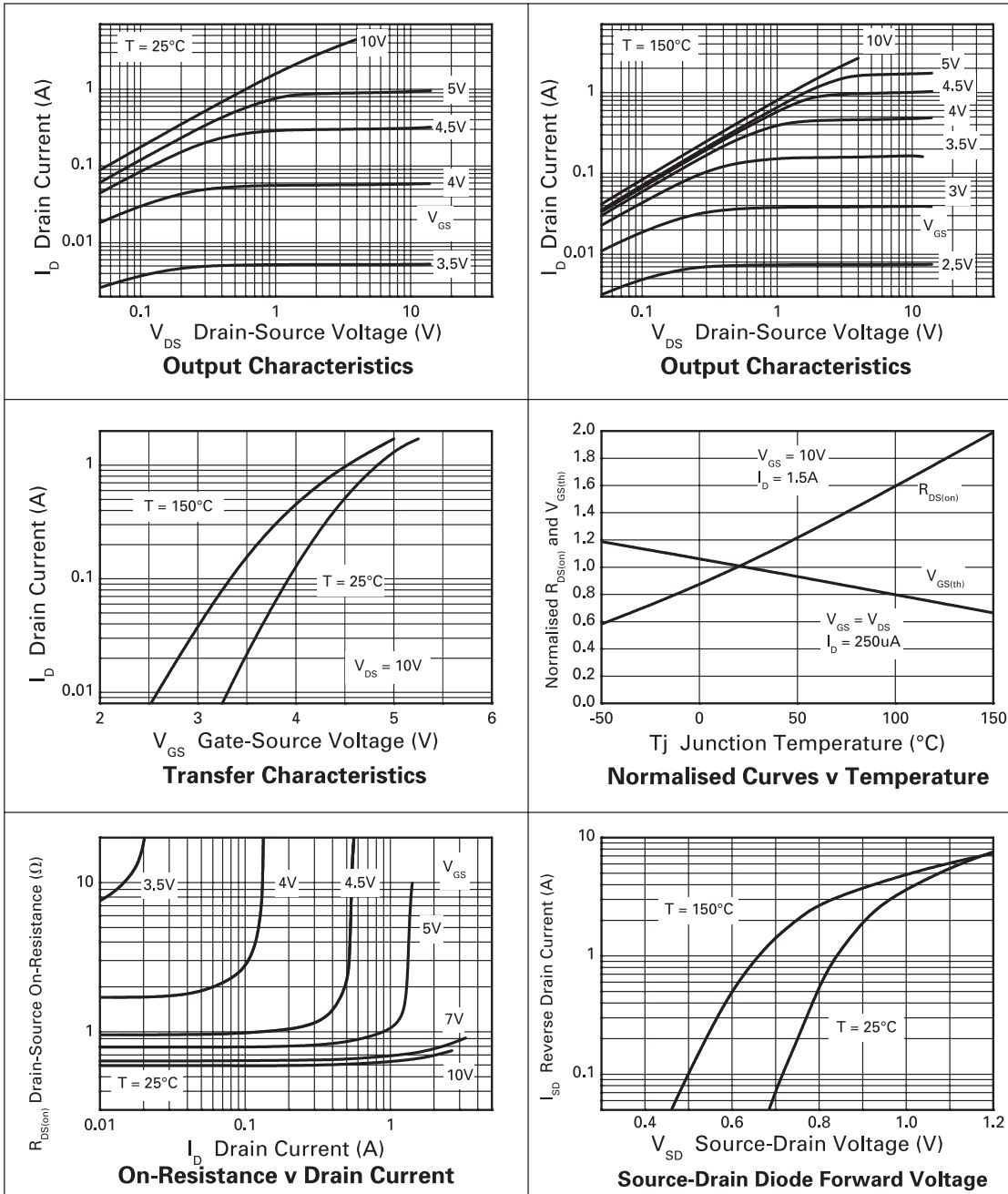
(3) Switching times measured with 50W source impedance and <5ns rise time on a pulse generator

HIGH VOLTAGE MOSFET (N-CHANNEL)

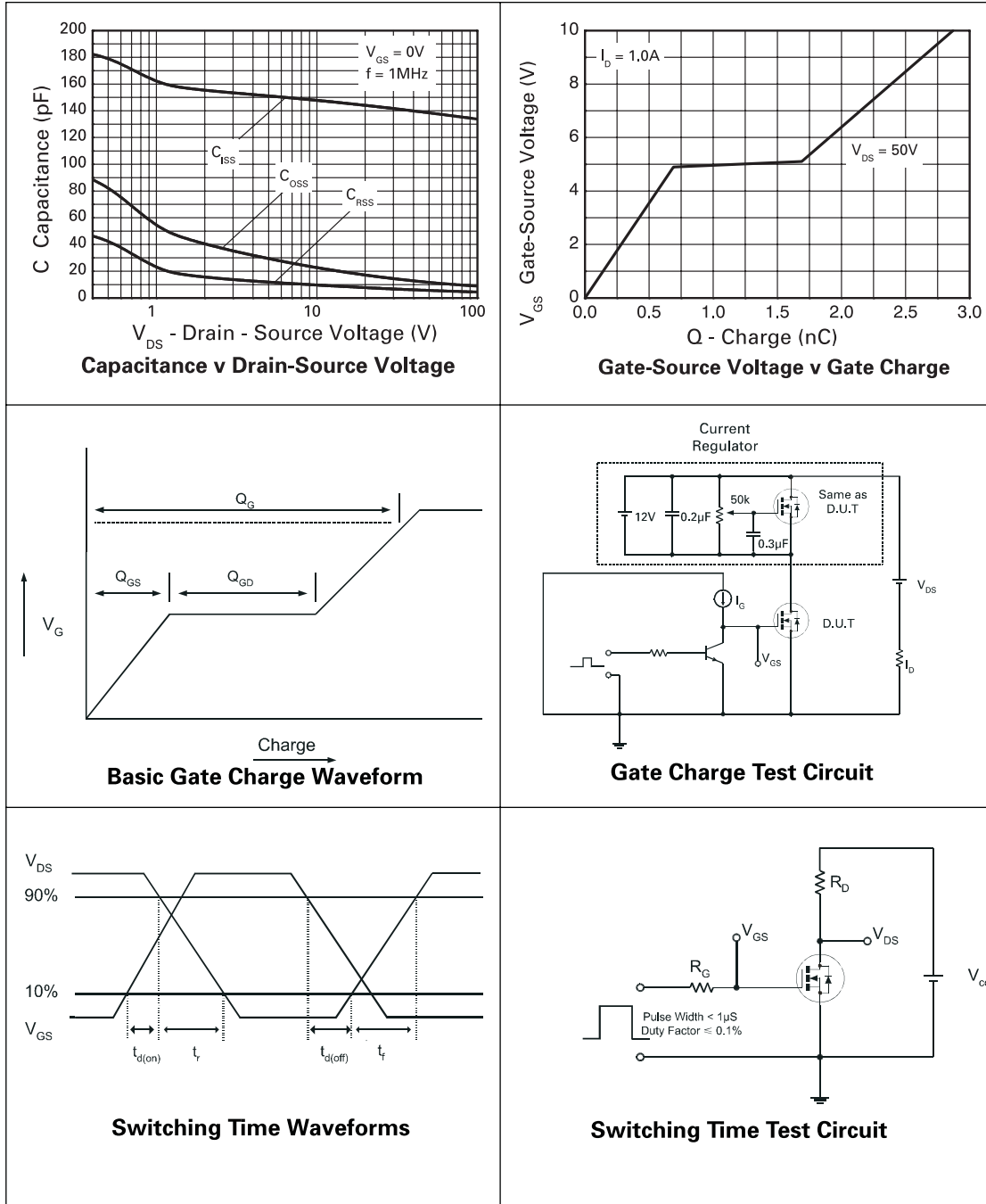
Typical Characteristics

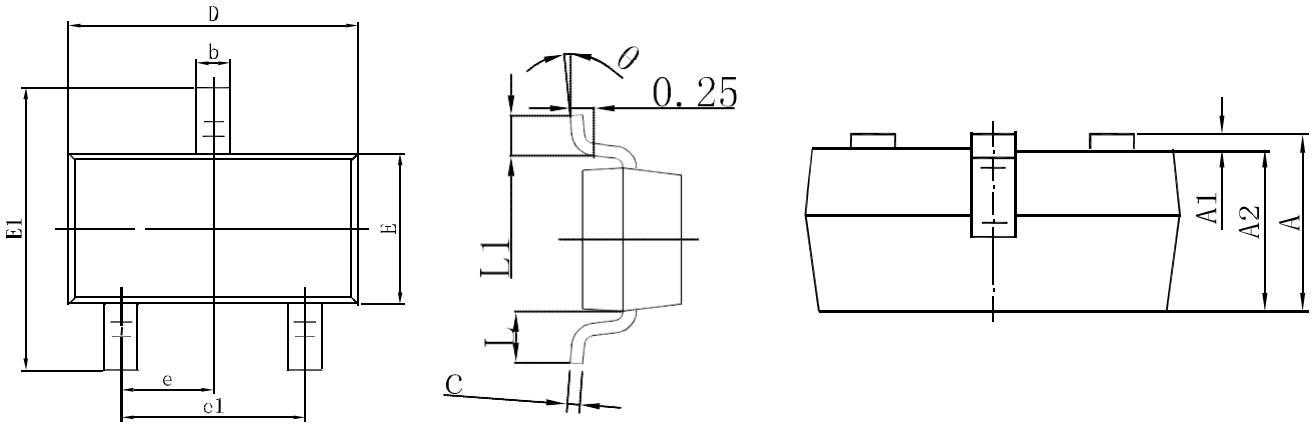


HIGH VOLTAGE MOSFET (N-CHANNEL)

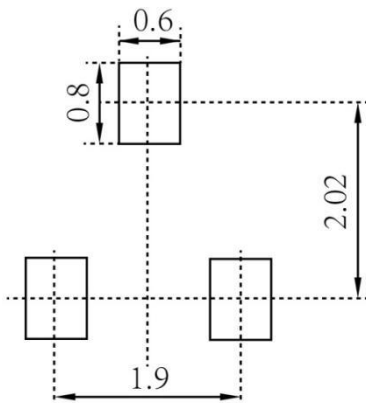


HIGH VOLTAGE MOSFET (N-CHANNEL)

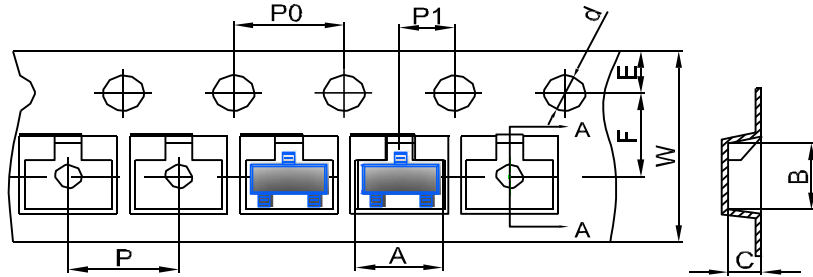


HIGH VOLTAGE MOSFET (N-CHANNEL)
SOT-23 Package Outline Dimensions


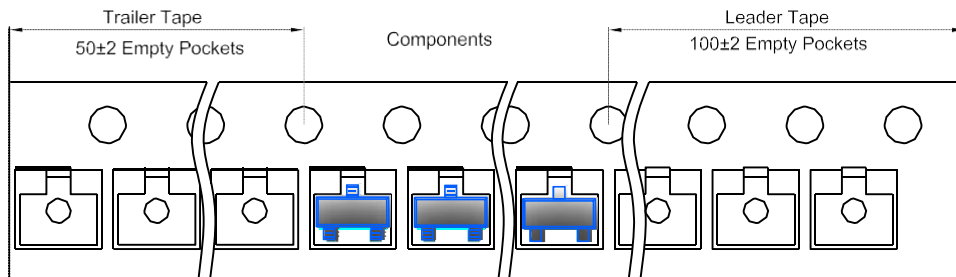
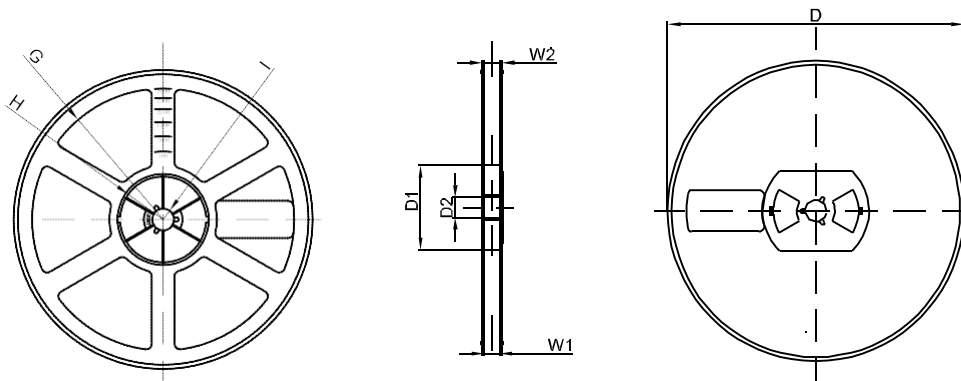
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

HIGH VOLTAGE MOSFET (N-CHANNEL)
SOT-23 Tape and Reel
SOT-23 Embossed Carrier Tape


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer

SOT-23 Reel


DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1